DATA SHEET

BFG591
NPN 7 GHz wideband transistor

Product specification
Supersedes data of November 1992

1995 Sep 04

NPN 7 GHz wideband transistor BFG591

FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability.

APPLICATIONS

Intended for applications in the GHz range such as MATV or CATV amplifiers and RF communications subscriber equipment.

DESCRIPTION

NPN silicon planar epitaxial transistor in a plastic, 4-pin SOT223 package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	emitter
4	collector

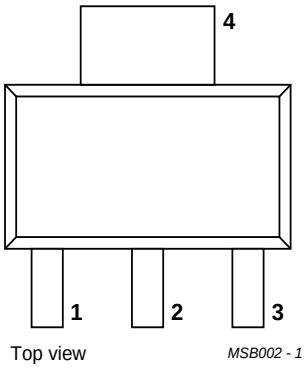


Fig.1 SOT223.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	–	15	V
I_C	collector current (DC)		–	–	200	mA
P_{tot}	total power dissipation	up to T_s = 80 °C; note 1	–	–	2	W
h_{FE}	DC current gain	I_C = 70 mA; V_{CE} = 8 V	60	90	250	
C_{re}	feedback capacitance	$I_C = I_c = 0$; V_{CE} = 12 V; f = 1 MHz	–	0.7	–	pF
f_T	transition frequency	I_C = 70 mA; V_{CE} = 12 V; f = 1 GHz	–	7	–	GHz
G_{UM}	maximum unilateral power gain	I_C = 70 mA; V_{CE} = 12 V; f = 900 MHz; T_{amb} = 25 °C	–	13	–	dB
$\lvert s_{21}\rvert^2$	insertion power gain	I_C = 70 mA; V_{CE} = 12 V; f = 900 MHz; T_{amb} = 25 °C	–	12	–	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	3	V
I_C	collector current (DC)		–	200	mA
P_{tot}	total power dissipation	up to T_s = 80 °C; note 1	–	2	W
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	note 1	35	K/W

Note to the Limiting values and Thermal characteristics

1. T_s is the temperature at the soldering point of the collector pin.

CHARACTERISTICS

T_j = 25 °C (unless otherwise specified).

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	I_C = 0.1 mA; I_E = 0	20	–	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	I_C = 10 mA; I_B = 0	15	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I_E = 0.1 mA; I_C = 0	3	–	–	V
I_{CBO}	collector-base leakage current	I_E = 0; V_{CB} = 10 V	–	–	100	nA
h_{FE}	DC current gain	I_C = 70 mA; V_{CE} = 8 V	60	90	250	
C_{re}	feedback capacitance	$I_B = I_b$ = 0; V_{CE} = 12 V; f = 1 MHz	–	0.7	–	pF
f_T	transition frequency	I_C = 70 mA; V_{CE} = 12 V; f = 1 GHz	–	7	–	GHz
G_{UM}	maximum unilateral power gain; note 1	I_C = 70 mA; V_{CE} = 12 V; f = 900 MHz; T_{amb} = 25 °C	–	13	–	dB
		I_C = 70 mA; V_{CE} = 12 V; f = 2 GHz; T_{amb} = 25 °C	–	7.5	–	dB
$\lvert s_{21}\rvert^2$	insertion power gain	I_C = 70 mA; V_{CE} = 12 V; f = 1 GHz; T_{amb} = 25 °C	–	12	–	dB
V_o	output voltage	note 2	–	700	–	mV

Notes

1. G_{UM} is the maximum unilateral power gain, assuming s_{12} is zero. $G_{UM} = 10 \log \frac{\lvert s_{21}\rvert^2}{(1-\lvert s_{11}\rvert^2)(1-\lvert s_{22}\rvert^2)}$ dB.
2. d_{im} = 60 dB (DIN45004B);
   $V_p = V_o$; $V_q = V_o$ –6 dB; $V_r = V_o$ –6 dB;
   f_p = 795.25 MHz; f_q = 803.25 MHz; f_r = 803.25 MHz; measured at $f_{(p+q-r)}$ = 793.25 MHz.

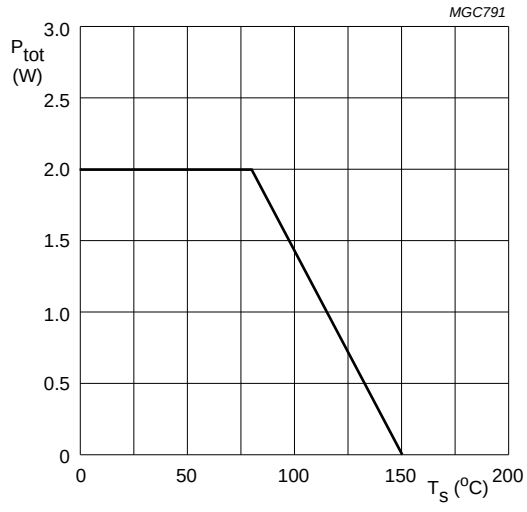
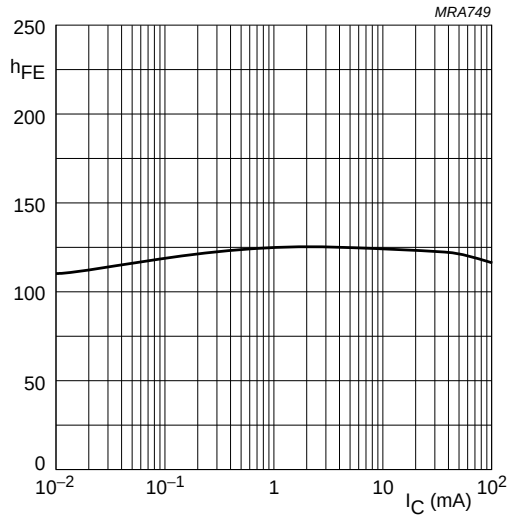
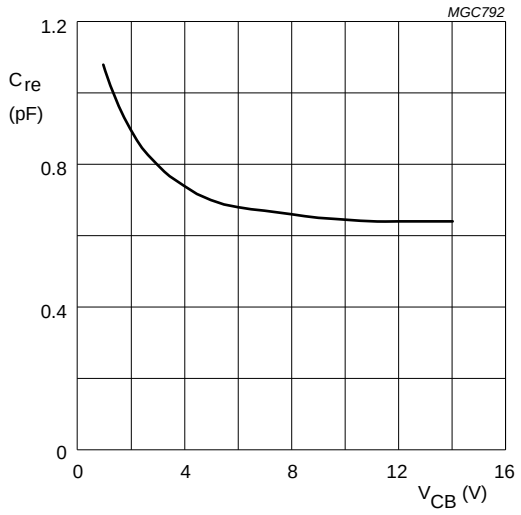


Fig.2 Power derating curve.



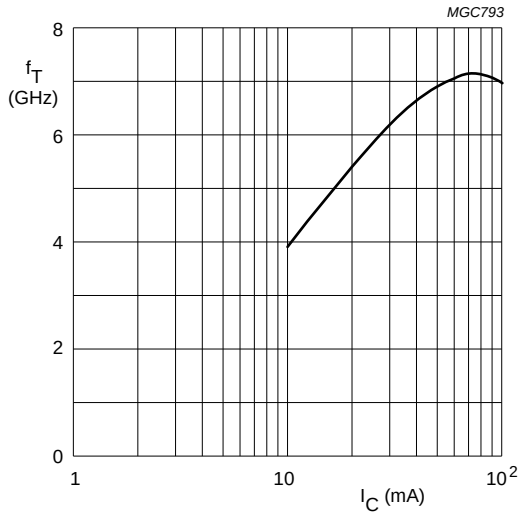
V_{CE} = 12 V.

Fig.3 DC current gain as a function of collector current, typical values.



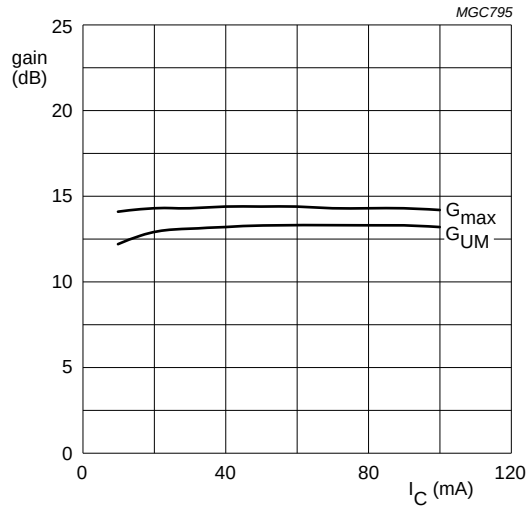
I_C = 0; f = 1 MHz.

Fig.4 Feedback capacitance as a function of collector-base voltage, typical values.



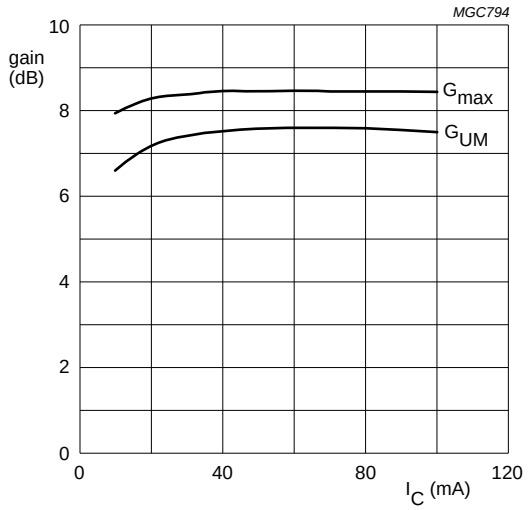
f = 1 GHz; V_{CE} = 12 V.

Fig.5 Transition frequency as a function of collector current, typical values.



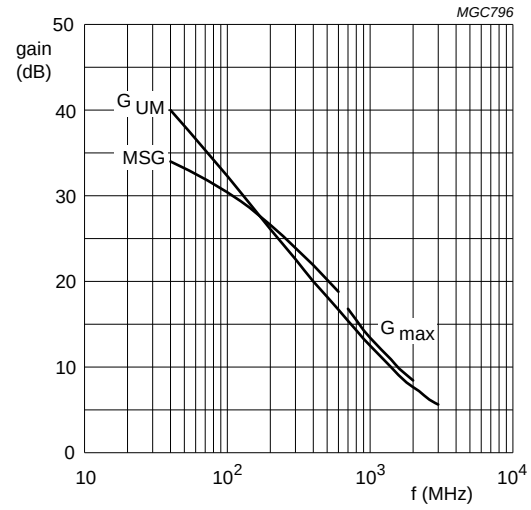
f = 900 MHz; V_{CE} = 12 V.

Fig.6 Gain as a function of collector current; typical values.



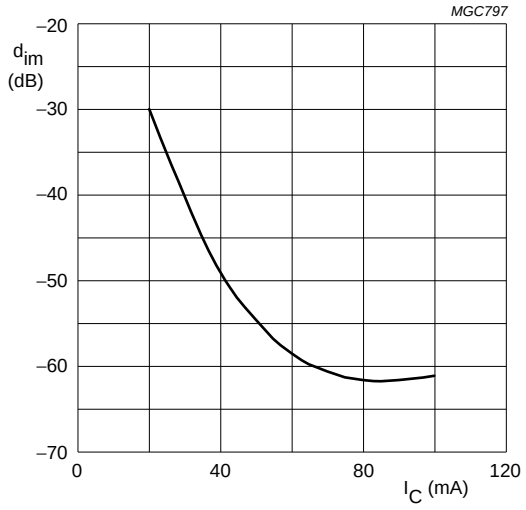
f = 2 GHz; V_{CE} = 12 V.

Fig.7 Gain as a function of collector current; typical values.



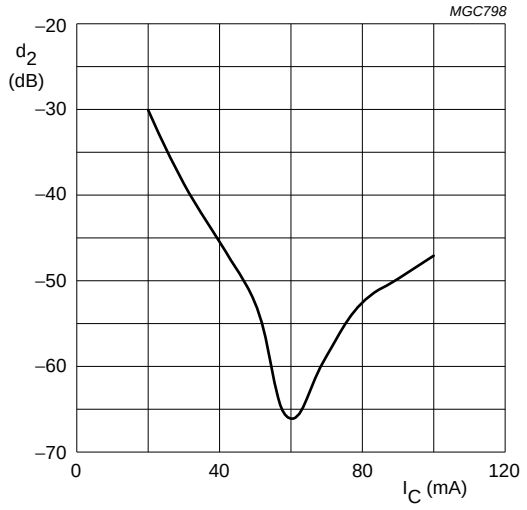
I_C = 70 mA; V_{CE} = 12 V.

Fig.8 Gain as a function of frequency; typical values.



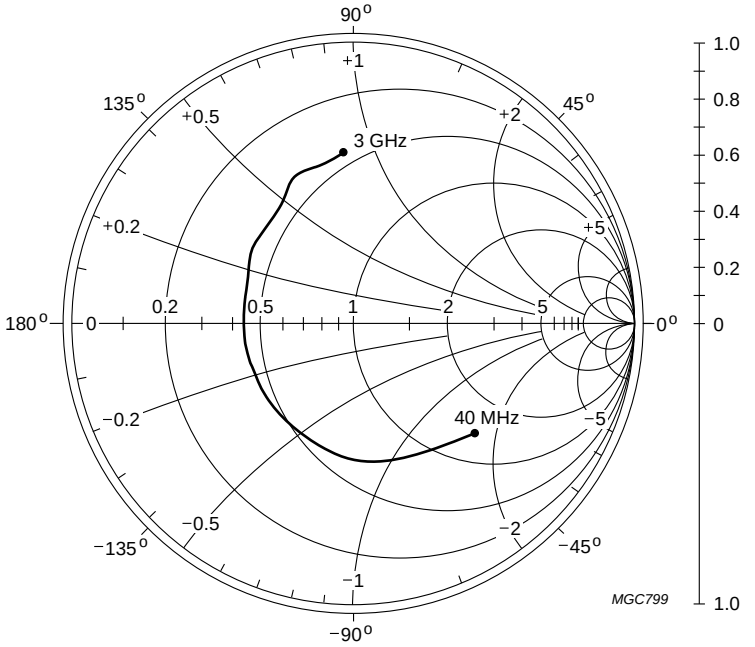
V_{CE} = 12 V; V_o = 700 mV; $f_{(p+q-r)}$ = 793.25 MHz.

Fig.9 Intermodulation distortion as a function of collector current; typical values.



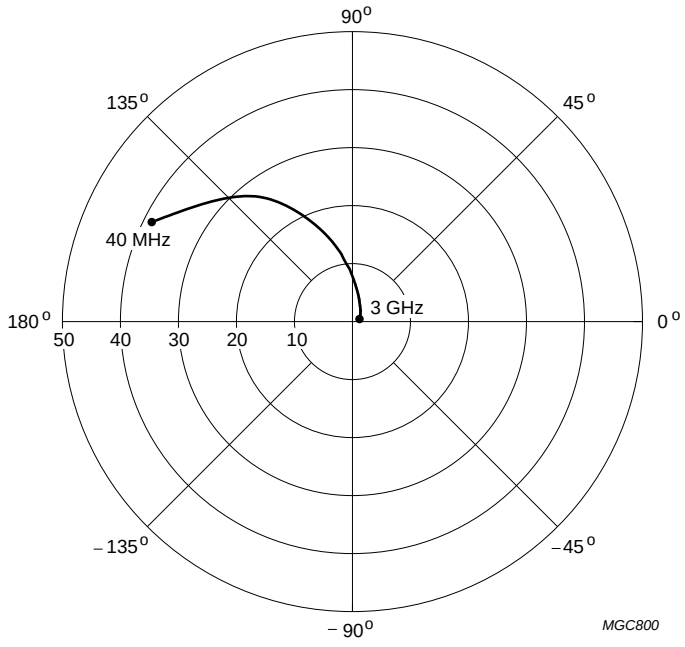
V_{CE} = 12 V; V_o = 316 mV; $f_{(p+q)}$ = 810 MHz.

Fig.10 Second order Intermodulation distortion as a function of collector current; typical values.



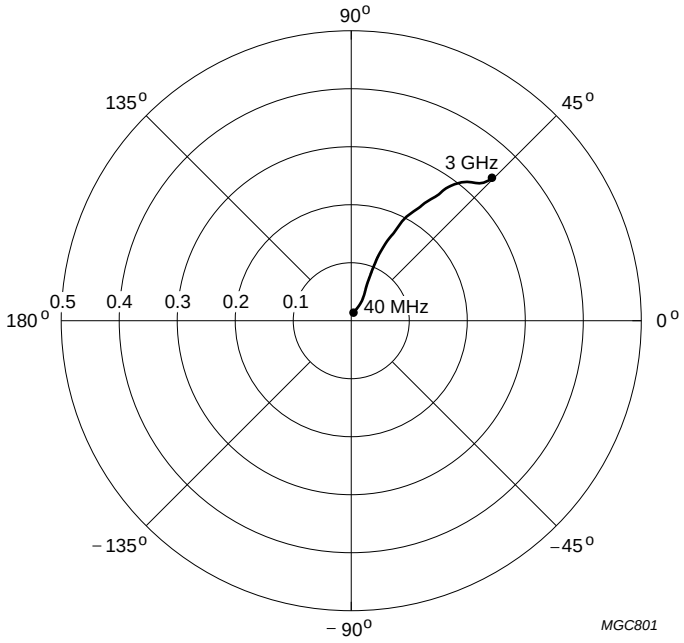
V_{CE} = 12 V; I_C = 70 mA; Z_o = 50 Ω.

Fig.11 Common emitter input reflection coefficient (s_{11}); typical values.



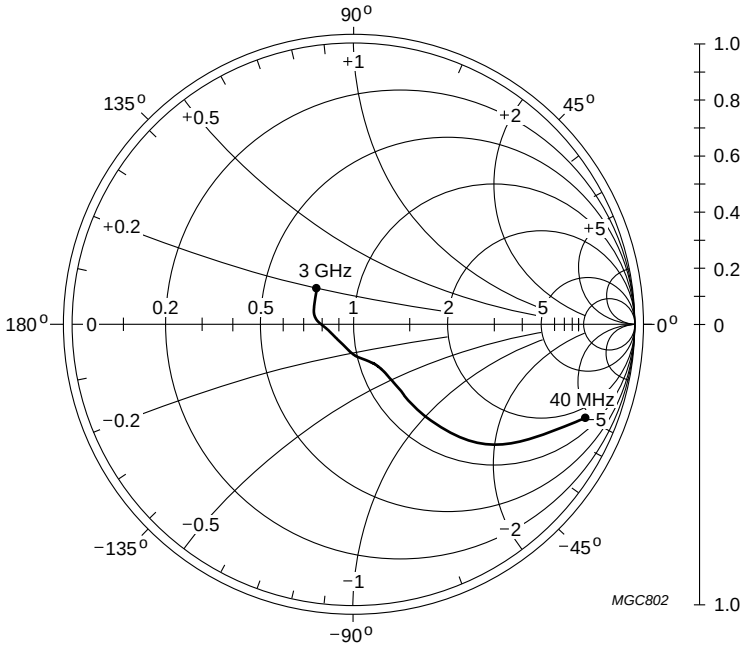
V_{CE} = 12 V; I_C = 70 mA.

Fig.12 Common emitter forward transmission coefficient (s_{21}); typical values.



V_{CE} = 12 V; I_C = 70 mA.

Fig.13 Common emitter reverse transmission coefficient (s_{12}); typical values.



V_{CE} = 12 V; I_C = 70 mA; Z_o = 50 Ω.

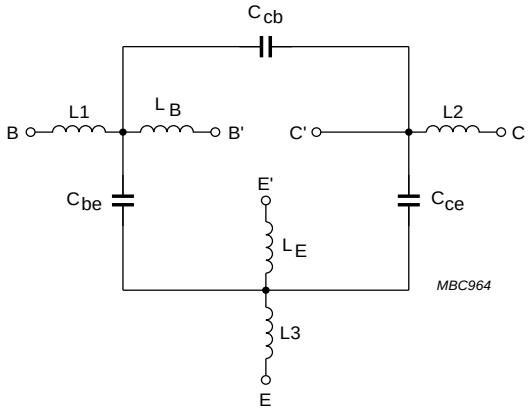
Fig.14 Common emitter output reflection coefficient (s_{22}); typical values.

SPICE parameters for the BFG591 crystal

SEQUENCE No.	PARAMETER	VALUE	UNIT
1	IS	1.341	fA
2	BF	123.5	–
3	NF	.988	m
4	VAF	75.85	V
5	IKF	9.656	A
6	ISE	232.2	fA
7	NE	2.134	–
8	BR	10.22	–
9	NR	1.016	–
10	VAR	1.992	V
11	IKR	294.1	mA
12	ISC	211.0	aA
13	NC	997.2	–
14	RB	5.00	Ω
15	IRB	1.000	μA
16	RBM	5.00	Ω
17	RE	1.275	Ω
18	RC	920.6	mΩ
19 (1)	XTB	0.000	–
20 (1)	EG	1.110	EV
21 (1)	XTI	3.000	–
22	CJE	3.821	pF
23	VJE	600.0	mV
24	MJE	348.5	m
25	TF	13.60	ps
26	XTF	71.73	–
27	VTF	10.28	V
28	ITF	1.929	A
29	PTF	0.000	deg
30	CJC	1.409	pF
31	VJC	219.4	mV
32	MJC	166.5	m
33	XCJ	2.340	m
34	TR	543.7	ns
35 (1)	CJS	0.000	F
36 (1)	VJS	750.0	mV
37 (1)	MJS	0.000	–
38	FC	733.2	m

Note

1. These parameters have not been extracted, the default values are shown.



$QL_B = 50$; $QL_E = 50$; $QL_{B,E}(f) = QL_{B,E}\sqrt{(f/f_c)}$;
f_c = scaling frequency = 1 GHz.

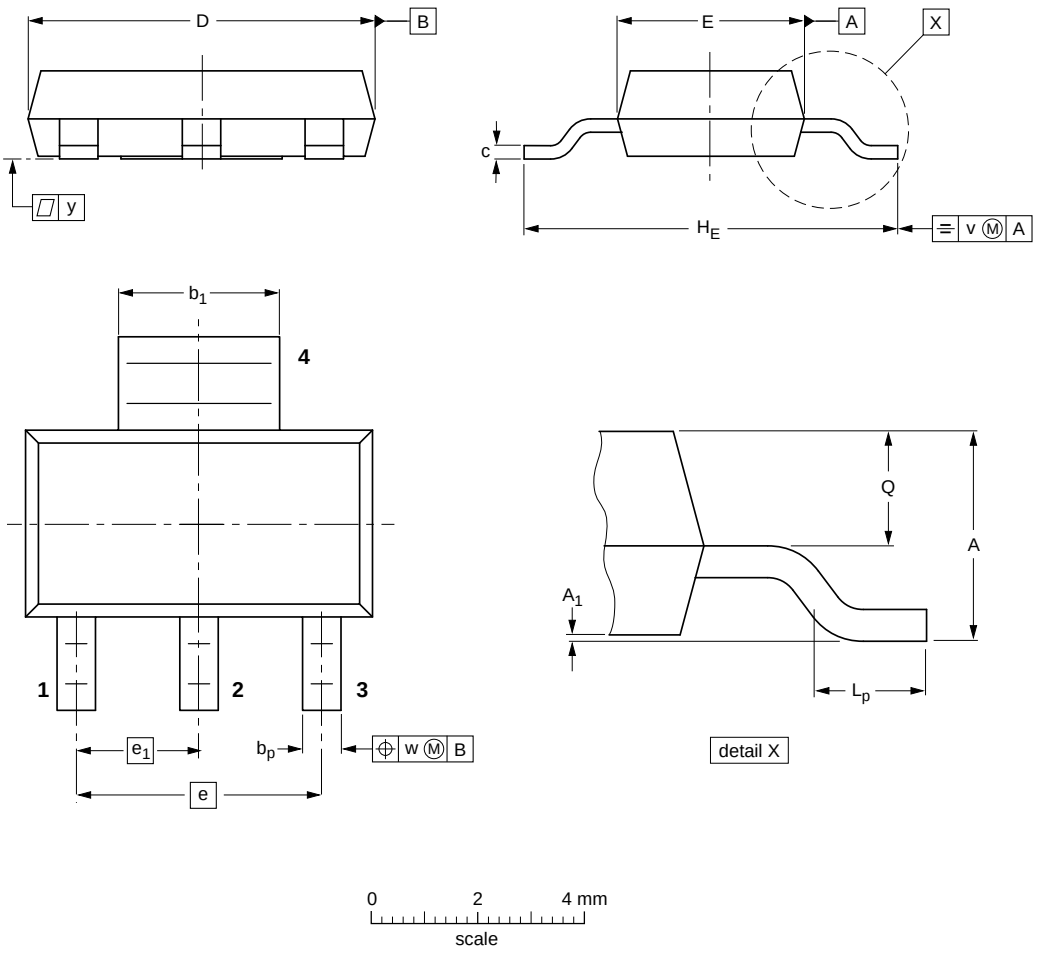
Fig.15 Package equivalent circuit SOT223.

List of components (see Fig.15)

DESIGNATION	VALUE	UNIT
C_{be}	182	fF
C_{cb}	16	fF
C_{ce}	249	fF
L1	0.025	nH
L2	1.19	nH
L3	0.60	nH
L_B	1.50	nH
L_E	0.50	nH

PACKAGE OUTLINE

Plastic surface-mounted package with increased heatsink; 4 leads **SOT223**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT223			SC-73			~~04-11-10~~ 06-03-16